

● General Description

The AGMH035N10C combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

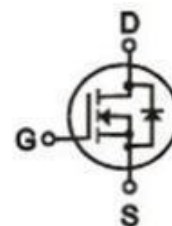
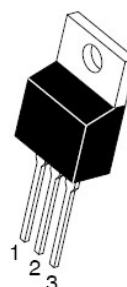
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
100V	3.6mΩ	150A

TO-220 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGMH035N10C	AGMH035N10C	TO-220	----	----	1000

Table 1. Absolute Maximum Ratings (TC=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	100	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	150	A
	Drain Current-Continuous(Tc=100°C)	105	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	600	A
PD	Maximum Power Dissipation(Tc=25°C)	208	w
	Maximum Power Dissipation(Tc=100°C)	84	w
EAS	Avalanche energy (Note 3)	540	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	60	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	0.6	°C/W

Table 3. Electrical Characteristics (TC=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	100	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=100V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	2.5	3.0	3.5	V
gFS	Forward Transconductance	VDS=5V,ID=20A	--	36	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=30A	--	3.6	4.25	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=50V,VGS=0V, F=1MHZ	--	3950	--	pF
Coss	Output Capacitance		--	1200	--	pF
Crss	Reverse Transfer Capacitance		--	27	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	0.77	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=50V, ID=75A,RGEN=5Ω	--	25	--	nS
tr	Turn-on Rise Time		--	33	--	nS
td(off)	Turn-Off Delay Time		--	95	--	nS
tf	Turn-Off Fall Time		--	75	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=50V, ID=75A	--	67.2	--	nC
Qgs	Gate-Source Charge		--	16.9	--	nC
Qgd	Gate-Drain Charge		--	16.9	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	150	A
VSD	Forward on Voltage	VGS=0V,IS=20A	--	--	1.2	V
trr	Reverse Recovery Time	IF=20A , dI/dt=100A/μs ,	--	82	--	ns
Qrr	Reverse Recovery Charge	TJ=25°C	--	180	--	nc

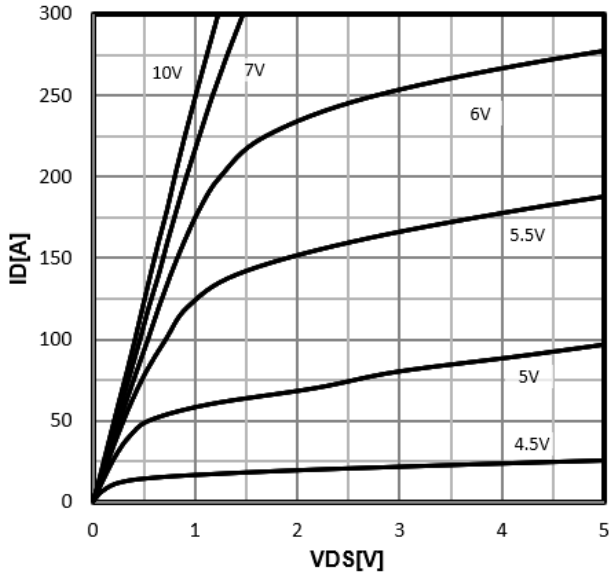
Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

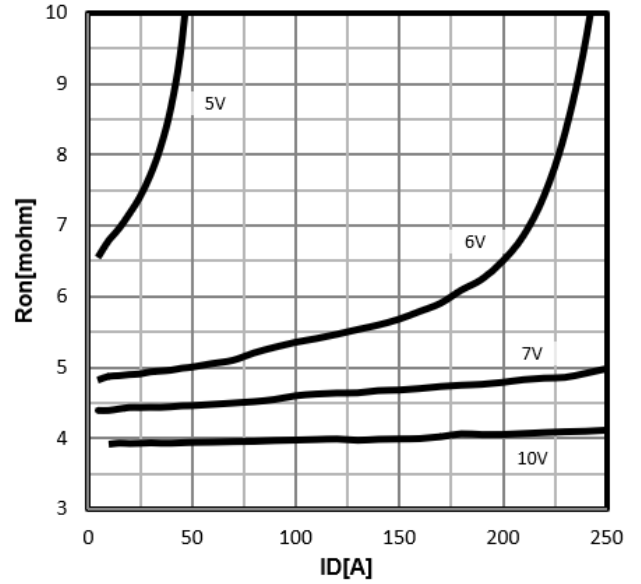
Notes 3.EAS condition: TJ=25°C

Characteristics Curve:
Typ. output characteristics

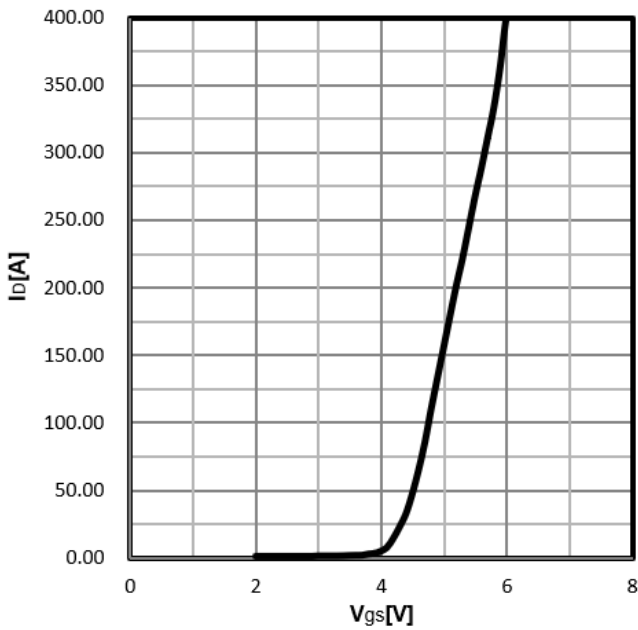
$$I_D = f(V_{DS})$$


Typ. drain-source on resistance

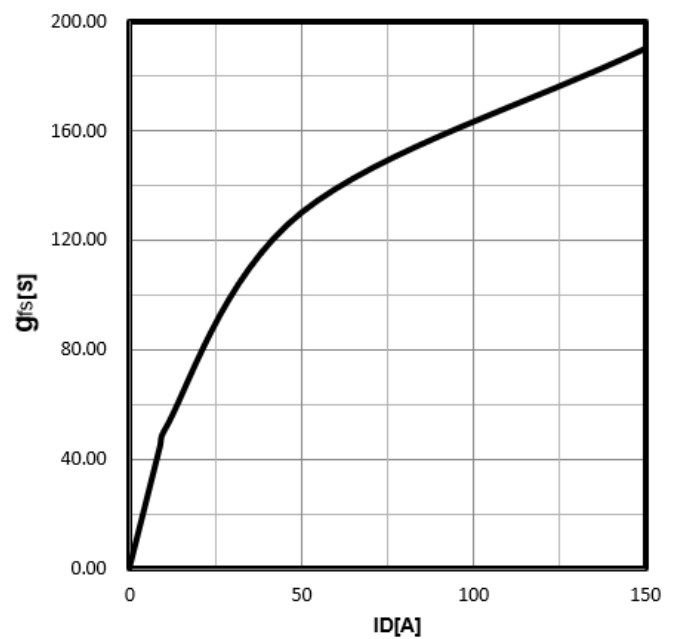
$$R_{DS(on)} = f(I_D)$$


Typ. transfer characteristics

$$I_D = f(V_{GS})$$

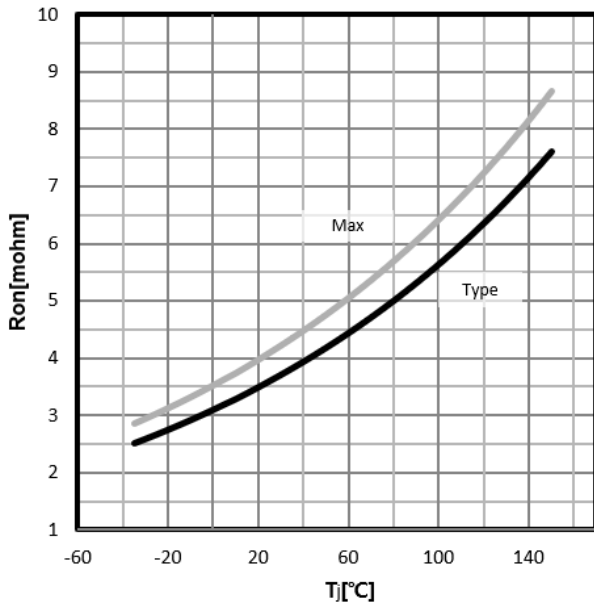

Typ. forward transconductance

$$g_{fs} = f(I_D)$$

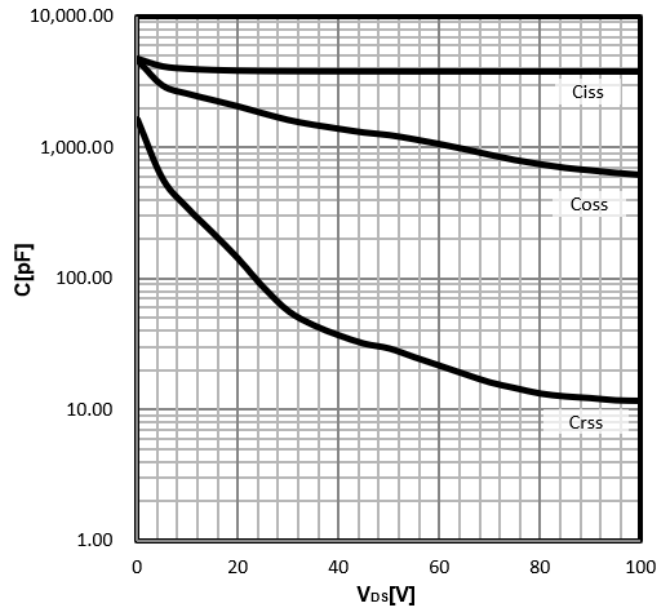


Drain-source on-state resistance

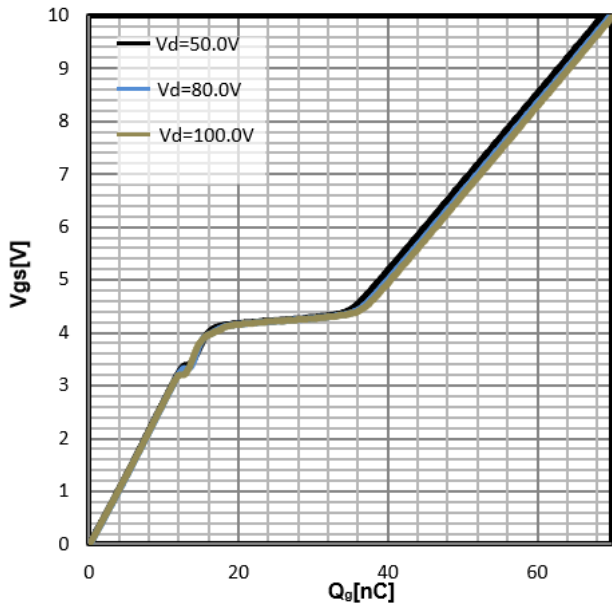
$$R_{DS(on)} = f(T_j); I_D = 75A; V_{GS} = 10V$$


Typ. capacitances

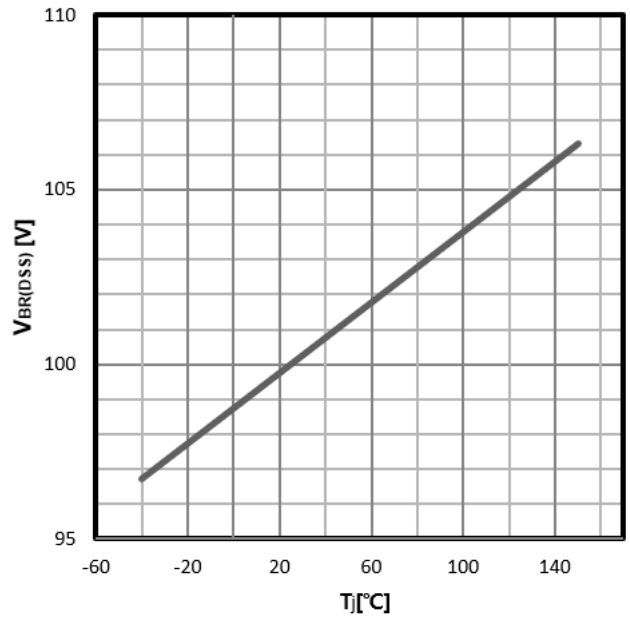
$$C = f(V_{DS}); V_{GS} = 0V; f = 1MHz$$


Typ. gate charge

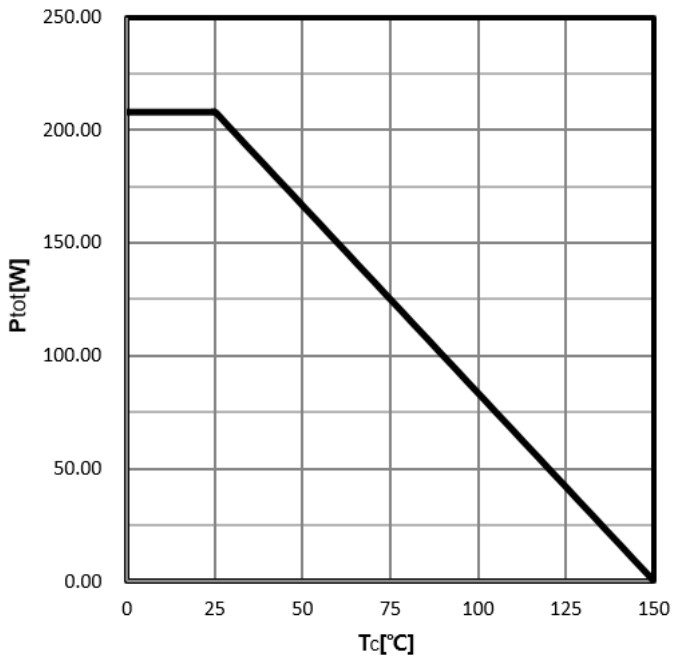
$$V_{GS} = f(Q_{gate})$$


Drain-source breakdown voltage

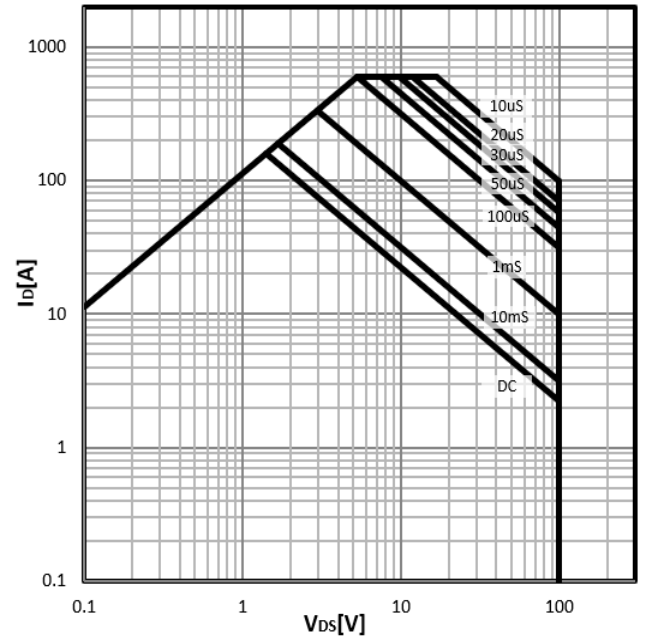
$$V_{BR(DSS)} = f(T_j); I_D = 250\mu A$$



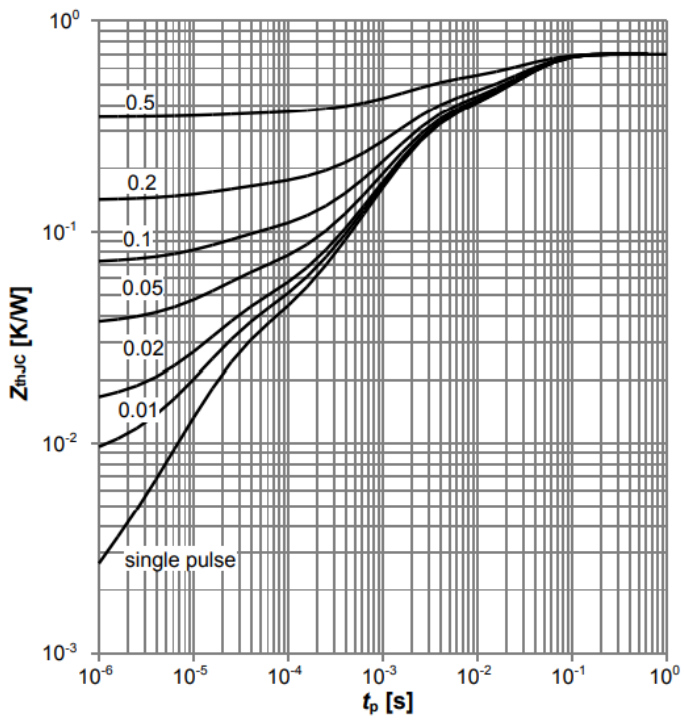
Power Dissipation
 $P_{tot}=f(T_j)$

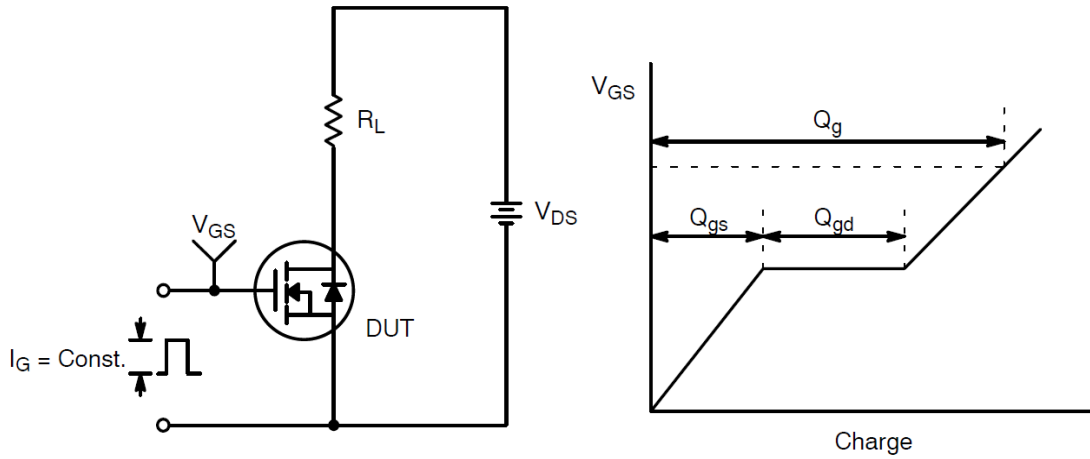
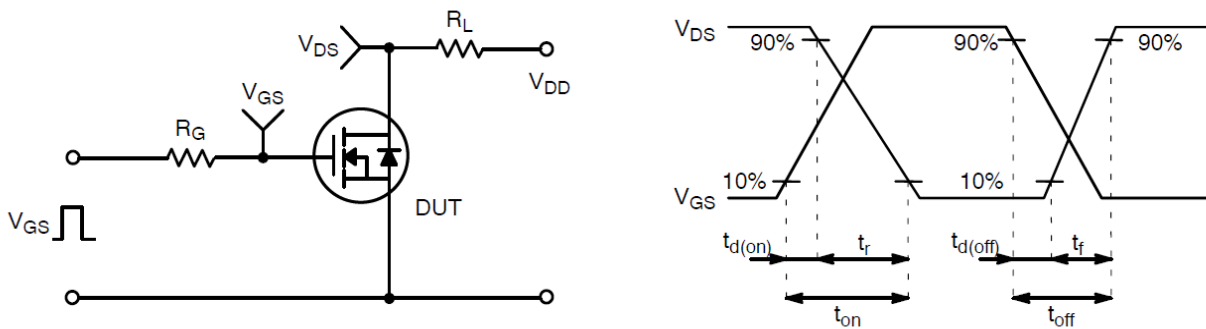
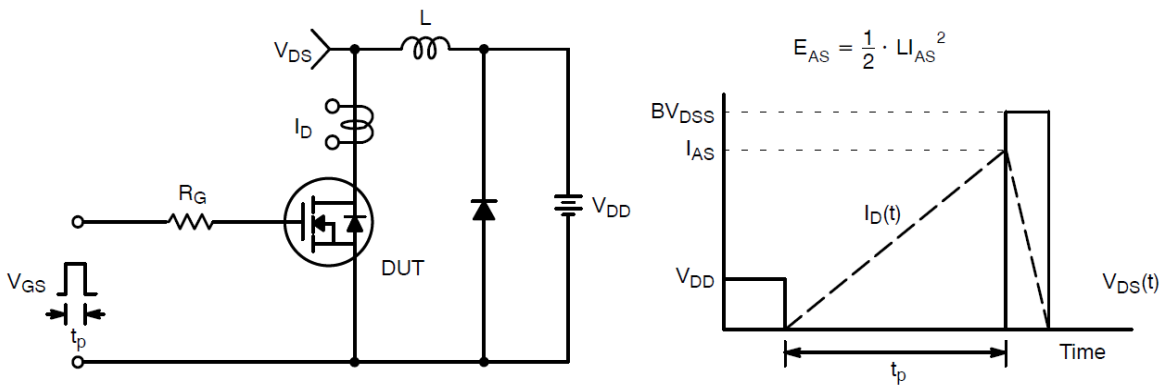


Safe operating area
 $I_D=f(V_{DS})$

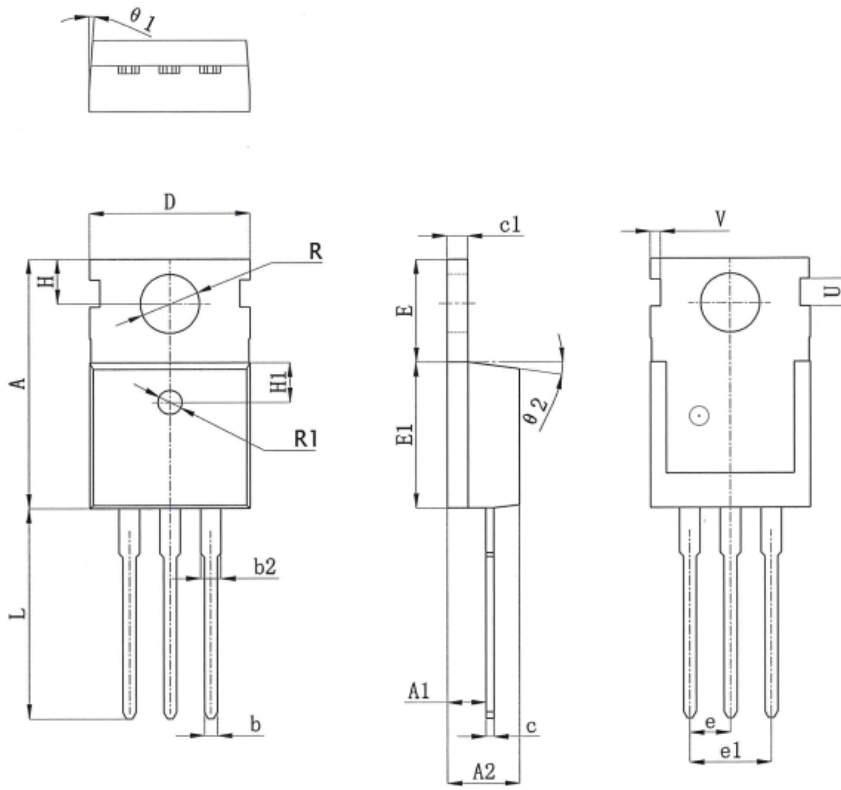


Max. transient thermal impedance
 $Z_{thJC}=f(t_p)$

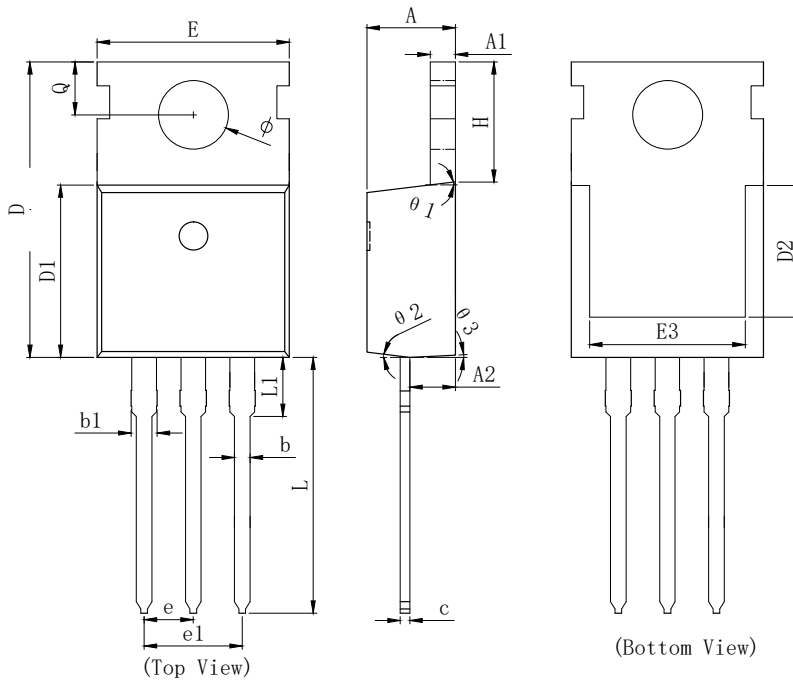


Test Circuit and Waveform:

Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching Test Circuit & Waveforms

TO220 PACKAGE INFORMATION



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	15.400	15.600	15.800
A1	2.350	2.400	2.500
A2	4.400	4.500	4.700
b	0.700	0.800	0.900
b2	1.180	1.310	1.440
c	0.480	0.500	0.560
c1	1.290	1.300	1.320
D	9.800	10.000	10.200
E	6.400	6.500	6.600
E1	9.000	9.100	9.200
e	2.420	2.540	2.660
e1	4.840	5.080	5.320
H	2.730	2.800	2.870
H1	2.400	2.500	2.600
L	13.020	13.370	13.720
R	3.500	3.600	3.730
R1	1.400	1.500	1.600
U	1.650	1.750	1.850
V	0.580	0.680	0.780
$\theta 1$	2°	2.5°	3°
$\theta 2$	6.5°	7°	7.5°



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	4.370	4.570	4.700
A1	1.250	1.300	1.400
A2	2.150	2.350	2.550
b	0.700	0.800	0.950
b1	1.170	1.270	1.470
c	0.450	0.500	0.600
D	15.100	15.600	16.100
D1	8.800	9.100	9.400
D2	5.500	6.300 REF	
E	9.700	10.000	10.300
E3	7.000	7.600 REF	
e	2.540 BSC		
e1	5.080 BSC		
L	13.200	13.500	13.800
L1		3.100	3.400
H	6.250	6.500	6.750
ϕ	3.400	3.600	3.800
Q	2.600	2.800	3.000
$\theta 1$	7° TYP		
$\theta 2$	7° TYP		
$\theta 3$	3° TYP		


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